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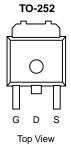
N-Channel 60 V (D-S) MOSFET

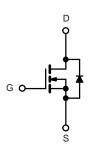
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a			
60	0.0093 at V _{GS} = 10 V	55			
00	0.0122 at V _{GS} = 4.5 V	50			

FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET
- Material categorization:







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage		V_{GS}	± 20	V		
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	I-	55			
Continuous Drain Current (1 _J = 175 C) ⁻¹	T _C = 100 °C	l _D	50 ^a			
Pulsed Drain Current	I _{DM}	165	A			
Continuous Source Current (Diode Conduction)	I _S	50 ^a				
Avalanche Current	I _{AS}	50				
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ		
Maximum Power Dissination	T _C = 25 °C	P _D	136	w		
Maximum Power Dissipation	T _A = 25 °C	T D	3 ^b , 8.3 ^{b, c}]		
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maniana la satisma ta Amelianta	t ≤ 10 sec	D	15	18		
Maximum Junction-to-Ambient ^a	Steady State	R _{thJA}	40	50	°C/W	
Maximum Junction-to-Case		R _{thJC}	0.85	1.1		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$

Rev. 1.1 1





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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static	•		•	•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1	·	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		V _{GS} = 10 V, I _D = 10 A		0.0093	0.011		
D : 0	D	V _{GS} = 10 V, I _D = 10 A, T _J = 125 °C		0.0103	0.0112		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A, T _J = 175 °C		0.0106	0.0127	Ω	
		V _{GS} = 4.5 V, I _D = 5 A		0.0122	0.0135		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		60		S	
Dynamic			•				
Input Capacitance	C _{iss}			2650			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		470		pF	
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Q_g			47	70		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC	
Gate-Drain Charge ^c	Q_{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V, R}_{L} = 0.6 \Omega$		15	25	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				165	Α	
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns	

Notes:

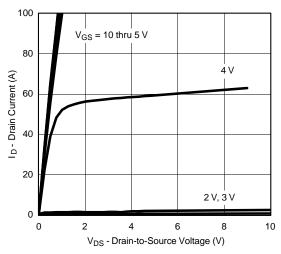
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

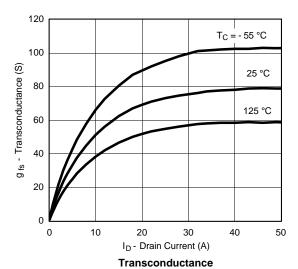


TYPICAL CHARACTERISTICS (25 °C unless noted)

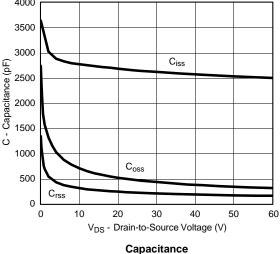
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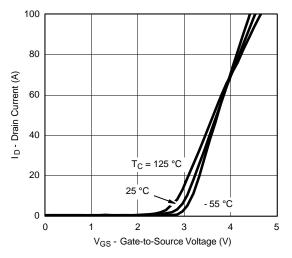


Output Characteristics

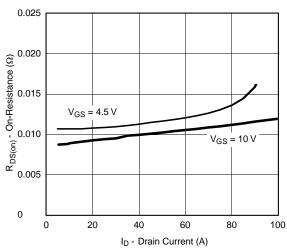


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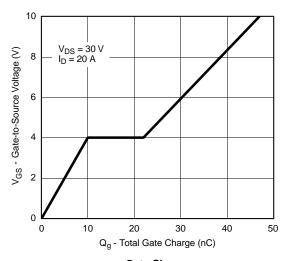




Transfer Characteristics



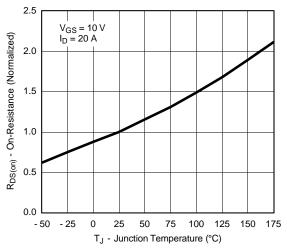
On-Resistance vs. Drain Current



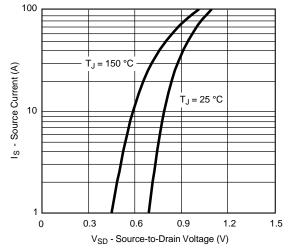
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



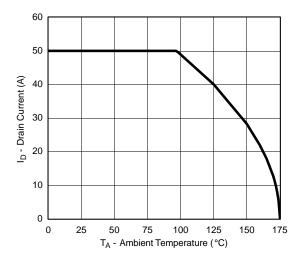
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

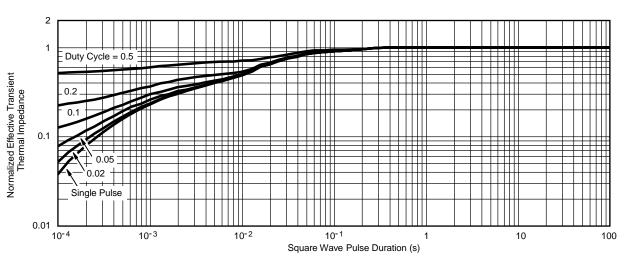


THERMAL RATINGS



1000 Limited by 10 µs 100 100 µs I_D - Drain Current (A) 10 1 ms 10 ms 100 ms DC T_C = 25 °C Single Pulse 0.1 0.01 L 0.1 100 $\label{eq:VDS} V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ ^*V_{GS} \text{ > minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$ Safe Operating Area

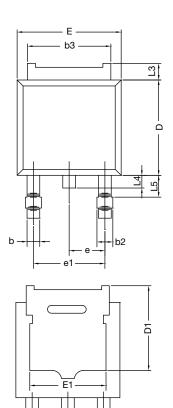
Maximum Drain Current vs. Ambient Temperature



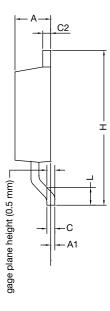
Normalized Thermal Transient Impedance, Junction-to-Case







Din-Tek SEMICONDUCTOR



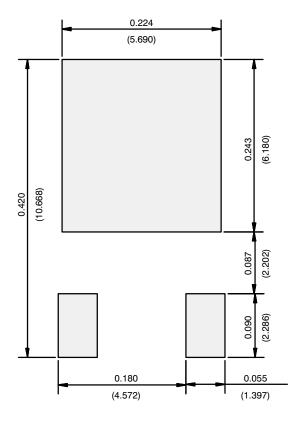
	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
Е	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28 BSC		0.090 BSC	
e1	4.56	BSC	0.180	BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
_	•	•	•	•

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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